

### **Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

### **Listing of Claims:**

1. (canceled)
2. (currently amended) The integrated circuit chip of ~~claim 1~~ claim 8, further comprising a passive component selected from the group comprising resistors, capacitors, and inductors.
3. (currently amended) The integrated circuit chip of ~~claim 1~~ claim 8, wherein the first electrically conductive material is polysilicon.
4. (currently amended) The integrated circuit chip of ~~claim 1~~ claim 8, wherein the second electrically conductive material is aluminum.
5. (currently amended) The integrated circuit chip of ~~claim 1~~ claim 8, wherein the spark gap cavity contains a noble gas for reducing the breakdown voltage of the electrostatic discharge protection device.
6. (currently amended) The integrated circuit chip of ~~claim 1~~ claim 8, wherein the substrate material is selected from the group comprising silicon, glass and a ceramic material.

7. (currently amended) A method of fabricating an integrated circuit chip comprising an integrated circuit and an electrostatic discharge protection device, the method comprising the steps of:

- a) providing a semiconductor substrate,
- b) depositing an insulating layer on the semiconductor substrate,
- c) depositing a first electrically conductive layer of a first electrically conductive material on said insulating layer,
- d) depositing a dielectric layer of a dielectric material directly on said first electrically conductive layer,
- e) etching the dielectric layer to form a window ~~space~~ contact windows for a center electrode ~~and a circumferential electrode,~~
- f) ~~depositing a mask,~~
- g) ~~etching a hollow groove into the first electrically conductive layer under the circumference of the contact window of the dielectric layer to form a toroidal spark gap cavity with a vertical gap between the insulating layer and the dielectric layer, wherein an exposed surface of the first electrically conductive layer forms a circumferential electrode,~~
- h) ~~depositing a layer of a second electrically conductive layer through the contact window of~~ to form the center electrode to mechanically in mechanical contact with the insulating layer and to seal the toroidal spark gap cavity with a lateral gap between the first and second electrically conductive layers, and through the contact window of the circumferential electrode to electrically contact the first electrically conductive layer, and
- i) connecting the center electrode to input circuit paths to be protected from electrostatic discharge and, and  
connecting the circumferential electrode to an electrostatic discharge path comprising either a connection to a circuit ground or a circuit supply voltage.

8. (new) An integrated circuit chip comprising:  
at least one integrated circuit; and  
an integrated electrostatic discharge protection device, the electrostatic discharge protection device comprising:  
an insulating layer disposed on a substrate layer, the insulating layer of an electrically insulating material to form a base layer of a toroidal spark gap cavity;  
a first electrically conductive layer disposed on the insulating layer, the first electrically conductive layer of a first electrically conductive material to form a circumferential electrode with an outer side wall to define a window for the toroidal spark gap cavity;  
a dielectric layer disposed on the first electrically conductive layer, the dielectric layer of a dielectric material to form a cover layer of the toroidal spark gap cavity; and  
a second electrically conductive layer partially disposed directly on the dielectric layer and extending into the window for the toroidal spark gap cavity to be partially disposed directly on the insulating layer, the second electrically conductive layer of a second electrically conductive material to form a center electrode with an inner side wall that is laterally separated from the outer side wall of the first conductive layer by the toroidal spark gap cavity.
9. (new) The integrated circuit chip of claim 8, wherein the dielectric layer extends at least partially over the window of the toroidal spark gap cavity formed by the first electrically conductive layer.
10. (new) The integrated circuit chip of claim 9, wherein the dielectric layer is vertically separated from the insulating layer by the toroidal spark gap cavity.
11. (new) The integrated circuit chip of claim 8, further comprising means for electrically connecting the center electrode to input circuit paths to be protected from electrostatic discharge.

12. (new) The integrated circuit chip of claim 8, further comprising means for electrically connecting the circumferential electrode to an electrostatic discharge path comprising a connection to a circuit ground or a circuit supply voltage.
13. (new) The integrated circuit chip of claim 8, wherein the toroidal spark gap cavity is an annular cavity defined by the inner side wall of the second electrically conductive layer, the outer side wall of the first electrically conductive layer, the base layer of the insulating layer, and the cover layer of the dielectric layer.
14. (new) The method of claim 7, wherein depositing the second electrically conductive layer further comprises at least partially depositing the second electrically conductive layer on and in direct contact with the dielectric layer.